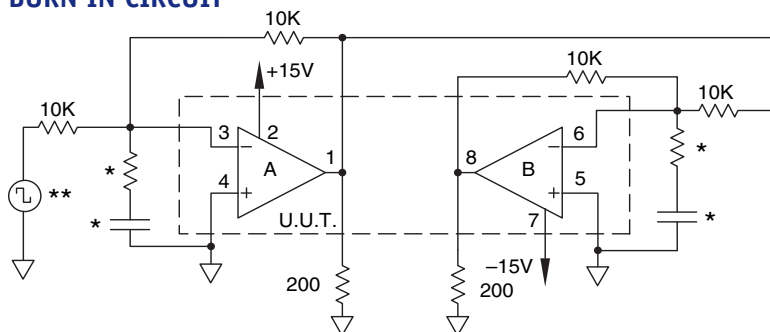


SG	PARAMETER	SYMBOL	TEMP.	POWER	TEST CONDITIONS	MIN	MAX	UNITS
1	Quiescent Current	I_O	25°C	±15	$V_{IN} = 0, A_V = 100$		30	mA
1	Input Offset Voltage	V_{OS}	25°C	±2.5	$V_{IN} = 0, A_V = 100$		10	mV
1	Input Offset Voltage	V_{OS}	25°C	±15	$V_{IN} = 0, A_V = 100$		10	mV
1	Input Offset Voltage	V_{OS}	25°C	±20	$V_{IN} = 0, A_V = 100$		14	mV
1	Input Bias Current + IN	$+I_B$	25°C	±15	$V_{IN} = 0$		1000	nA
1	Input Bias Current -IN	$-I_B$	25°C	±15	$V_{IN} = 0$		1000	nA
1	Input Offset Current	I_{OS}	25°C	±15	$V_{IN} = 0$		500	nA
3	Quiescent Current	I_O	-55°C	±15	$V_{IN} = 0, A_V = 100$		30	mA
3	Input Offset Voltage	V_{OS}	-55°C	±2.5	$V_{IN} = 0, A_V = 100$		14	mV
3	Input Offset Voltage	V_{OS}	-55°C	±15	$V_{IN} = 0, A_V = 100$		14	mV
3	Input Offset Voltage	V_{OS}	-55°C	±20	$V_{IN} = 0, A_V = 100$		18	mV
3	Input Bias Current + IN	$+I_B$	-55°C	±15	$V_{IN} = 0$		1000	nA
3	Input Bias Current -IN	$-I_B$	-55°C	±15	$V_{IN} = 0$		1000	nA
3	Input Offset Current	I_{OS}	-55°C	±15	$V_{IN} = 0$		500	nA
2	Quiescent Current	I_O	125°C	±15	$V_{IN} = 0, A_V = 100$		40	mA
2	Input Offset Voltage	V_{OS}	125°C	±2.5	$V_{IN} = 0, A_V = 100$		15	mV
2	Input Offset Voltage	V_{OS}	125°C	±15	$V_{IN} = 0, A_V = 100$		15	mV
2	Input Offset Voltage	V_{OS}	125°C	±20	$V_{IN} = 0, A_V = 100$		19	mV
2	Input Bias Current + IN	$+I_B$	125°C	±15	$V_{IN} = 0$		1000	nA
2	Input Bias Current -IN	$-I_B$	125°C	±15	$V_{IN} = 0$		1000	nA
2	Input Offset Current	I_{OS}	125°C	±15	$V_{IN} = 0$		500	nA
4	Output Voltage $I_O = 2A$	V_O	25°C	±9.5	$R_L = 3\Omega$	6.0		V
4	Output Voltage $I_O = 100mA$	V_O	25°C	±11	$R_L = 100\Omega$	9.9		V
4	Output Voltage $I_O = 1A$	V_O	25°C	±4.8	$R_L = 3\Omega$	2.8		V
4	Stability/Noise	E_N	25°C	±15	$R_L = 500\Omega, A_V = 1, C_L = 1.5nF$		1.0	mV
4	Crosstalk	XTLK	25°C	±15	$R_L = 3\Omega$	50		dB
4	Slew Rate	SR	25°C	±15	$R_L = 500\Omega$	.5		V/ μ S
4	Open Loop Gain	A_{OL}	25°C	±15	$R_L = 500\Omega, F = 10Hz$	75		dB
4	Common-mode Rejection	CMR	25°C	±17	$R_L = 500\Omega, V_{CM} = \pm 14V$	60		dB
6	Output Voltage $I_O = 2A$	V_O	-55°C	±9.5	$R_L = 3\Omega$	6.0		V
6	Output Voltage $I_O = 100mA$	V_O	-55°C	±11	$R_L = 100\Omega$	9.9		V
6	Output Voltage $I_O = 1A$	V_O	-55°C	±4.8	$R_L = 3\Omega$	2.8		V
6	Stability/Noise	E_N	-55°C	±15	$R_L = 500\Omega, A_V = 1, C_L = 1.5nF$		1.0	mV
6	Slew Rate	SR	-55°C	±15	$R_L = 500\Omega$	.5		V/ μ S
6	Open Loop Gain	A_{OL}	-55°C	±15	$R_L = 500\Omega, F = 10Hz$	75		dB
6	Common-mode Rejection	CMR	-55°C	±17	$R_L = 500\Omega, V_{CM} = \pm 14V$	60		dB
5	Output Voltage $I_O = 1A$	V_O	125°C	±4.8	$R_L = 3\Omega$	2.8		V
5	Output Voltage $I_O = 100mA$	V_O	125°C	±11	$R_L = 100\Omega$	9.9		V
5	Output Voltage $I_O = 750mA$	V_O	125°C	±4.0	$R_L = 3\Omega$	2.25		V
5	Stability/Noise	E_N	125°C	±15	$R_L = 500\Omega, A_V = 1, C_L = 1.5nF$		1.0	mV
5	Slew Rate	SR	125°C	±15	$R_L = 500\Omega$	.5		V/ μ S
5	Open Loop Gain	A_{OL}	125°C	±15	$R_L = 500\Omega, F = 10Hz$	75		dB
5	Common-mode Rejection	CMR	125°C	±17	$R_L = 500\Omega, V_{CM} = \pm 14V$	60		dB

BURN IN CIRCUIT



* These components are used to stabilize device due to poor high frequency characteristics of burn in board.

** Input signals are calculated to result in internal power dissipation of approximately 2.1W at case temperature = 125°C.